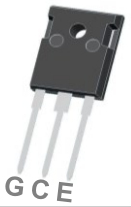
# CGWT30N65F2KAD

## CGWT30N65F2KAD

| $V_{CE}$ | Ic (Tc=100℃) | $V_{CE(sat)}$ |
|---|---|---|
| 650V | 30A | 1.62V |

**TO-247**




## DESCRIPTION

The CGWT30N65F2KAD is used SZCJ 's second generation IGBT technology, has advanced Trench and FS(Field Stop) Structure，it's with high application frequent, low Collector-Emitter Saturation Voltage and switching loss, can easy to use in parallel.

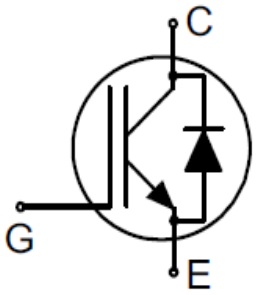
## Features

- 650V breakdown Voltage
- Low Vce(sat) and positive temperature coefficient
- High speed switching，Low switching loss
- With fast and soft recovery freewheeling diode
- Good EMI behavior

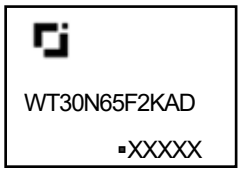
## Application

- UPS application
- PFC application
- Solar Inverter
- Power Storage
- Servo
- Welder

## EQUIVALENT CIRCUIT




## MARKING




WT30N65F2KAD = Device code

Solid dot = Green molding compound device, if none, the normal device

XXXXX = Code

| Order Code | Package | Marking | Parking |
|---|---|---|---|
| CGWT30N65F2KAD | TO-247 | WT30N65F2KAD | Tube |

感谢您的支持，如需要完整规格书，请联系：<igbt.list@szcjsemi.com >，谢谢!

Thank you for your support. If you need a complete datasheet, please contact:

<igbt.list@szcjsemi.com >. Thank you!